

Title (en)

A METHOD FOR FABRICATING NANOGAP AND NANOGAP SENSOR

Title (de)

VERFAHREN ZUR ERZEUGUNG EINES NANOSPALTS UND NANOSPALTSSENSOR

Title (fr)

PROCEDE POUR FABRIQUER UN NANO-INTERVALLE ET CAPTEUR DE NANO-INTERVALLE

Publication

**EP 1938364 A4 20110518 (EN)**

Application

**EP 06783773 A 20060905**

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Abstract (en)

[origin: WO2007046582A1] The present invention relates to a method of fabricating a nanogap and a nanogap sensor, and to a nanogap and a nanogap sensor fabricated using the method. The present invention relates to a method of fabricating a nanogap and a nanogap sensor, which can be realized by an anisotropic etching using a semiconductor manufacturing process. According to the method of present invention, the nanogap and nanogap sensor can be simply and cheaply produced in large quantities.

IPC 8 full level

**B81C 1/00** (2006.01)

CPC (source: EP)

**B81C 1/00087** (2013.01)

Citation (search report)

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- [A] EP 1366860 A1 20031203 - ASIA PACIFIC MICROSYSTEM INC [TW]
- [X] HASHIOKA S ET AL: "FABRICATION TECHNIQUE FOR PREPARING NANOGAP ELECTRODES BY CONVENTIONAL SILICON PROCESSES", JAPANESE JOURNAL OF APPLIED PHYSICS, JAPAN SOCIETY OF APPLIED PHYSICS, JP, vol. 44, no. 6A, 1 June 2005 (2005-06-01), pages 4213 - 4215, XP001502351, ISSN: 0021-4922, DOI: 10.1143/JJAP.44.4213
- [A] STORM A J ET AL: "FABRICATION OF SOLID-STATE NANOPORES WITH SINGLE-NANOMETRE PRECISION", NATURE MATERIALS, NATURE PUBLISHING GROUP, LONDON, GB, vol. 2, no. 8, 13 July 2003 (2003-07-13), pages 537 - 540, XP008046585, ISSN: 1476-4660, DOI: 10.1038/NMAT941
- See references of WO 2007046582A1

Citation (examination)

SHINGI HASHIOKA ET AL: "Fabrication Technique for Preparing Nanogap Electrodes by Conventional Silicon Processes", JAPANESE JOURNAL OF APPLIED PHYSICS, vol. 44, no. 6A, 1 June 2005 (2005-06-01), JP, pages 4213 - 4215, XP055395549, ISSN: 0021-4922, DOI: 10.1143/JJAP.44.4213

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